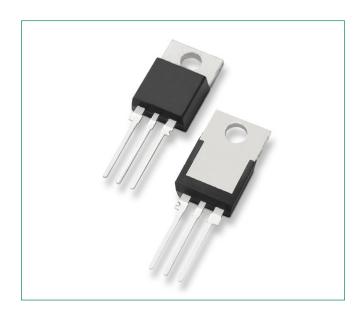


MCR69-2, MCR69-3





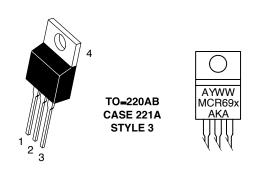
Description

Designed for overvoltage protection in crowbar circuits.

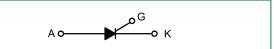
Features

- Glass-Passivated Junctions for Greater Parameter Stability and Reliability
- Center-Gate Geometry for Uniform Current Spreading Enabling High Discharge Current
- Small Rugged, Thermowatt Package Constructed for Low Thermal Resistance and Maximum Power Dissipation and Durability
- High Capacitor Discharge Current, 750 Amps
- Pb-Free Packages are Available

Pin Out



Functional Diagram



Pin Assignment			
1	Cathode		
2	Anode		
3	Gate		
4	Anode		

Additional Information







Resources



Samples



Maximum Ratings (T₁ = 25°C unless otherwise noted)

Circuit Fusing Considerations (t = 8.3 ms)

Operating Junction Temperature Range

Storage Temperature Range

Mounting Torque

Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, T₁ = 125°C)

Forward Peak Gate Current (Pulse Width \leq 1.0 μ s, $T_c = 85$ °C)

Forward Average Gate Power (t = 8.3 ms, $T_c = 80^{\circ}\text{C}$)

Rating	Part Number	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1)	MCR169-2	V _{DRM,}	50	V	
$(T_J = -40 \text{ to } +125^{\circ}\text{C}, \text{ Gate Open})$	MCR69-3	V _{RRM}	100		
Peak Discharge Current (Note 2)			750	А	
On-State RMS Current (180° Conduction Angles; T _c = 85°C)			25	А	
Average On-State Current (180° Conduction Angles; $T_c = 80$	I _{T(AV)}	16	А		

300

375

2.0

20

-40 to +125

-40 to +150

8.0

I_{TSM}

 I^2t

 I_{GM}

 P_GM

 $T_{\rm J}$

 $\mathsf{T}_{\mathsf{stg}}$

Α

A²sec

Α

W

°C

 $^{\circ}C$

in. lb.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall
 not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage
 ratings of the devices are exceeded.
- 2. Ratings apply for tw = 1 ms. See Figure 1 for ITM capability for various duration of an exponentially decaying current waveform, tw is defined as 5 time constants of an exponentially decaying current pulse.
- 3. Test Conditions: $I_{\rm G}$ = 150 mA, $V_{\rm D}$ = Rated $V_{\rm DRM'}$ $I_{\rm TM}$ = Rated Value, $T_{\rm J}$ = 125°C.

Thermal Characteristics

Characterstic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R _{eJC}	1.5	°C/W
Thermal Resistance, Junction-to-Ambient	R _{eJA}	60	
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T _L	260	°C



Electrical Characteristics - **OFF** $(T_j = 25^{\circ}C \text{ unless otherwise noted})$

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T _J = 25°C	l _{DRM}	-	-	10	μΑ
$(V_{AK} = V_{DRM} = V_{RRM}; Gate Open)$	T _J = 125°C	I _{RRM}	-	-	2.0	mA

Electrical Characteristics - ON

Characteristic		Symbol	Min	Тур	Max	Unit
	(Note 4) (I _{TM} = 50 A)		_	_	1.8	- V
Peak Forward On-State Voltage	(I _{TM} = 750 A, tw = 1 ms) (Note 5)	V _{TM}	_	6.0	-	
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}, R_L = 100 \text{ C}$	Ω)	I _{GT}	2.0	7.0	30	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ Vdc}$, $R_L = 100 \Omega$)		V _{GT}	0.5	0.65	1.0	V
Gate Non-Trigger Voltage (Continuous dc) ($V_D = 12 \text{ Vdc}, R_L = 100 \Omega, T_J - 125^{\circ}\text{C}$)		$V_{\rm GD}$	0.2	0.40	-	V
Holding Current (V _D = 12 Vdc, Initiating Current = 200 mA, Gate Open)		I _H	3.0	15	50	mA
Latch Current $(V_D = 12 V_{DC'} I_G = 150 \text{ mA})$		I _L	_	_	60	mA
Gate Controlled Turn-On Time (Note 6) (V_D = Rated $V_{DRM'}$ I_G = 150 mA) (I_{TM} = 50 A Peak)		t _{gt}	_	1.0	_	μs

Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate-of-Rise of Off-State Voltage $(V_D = Rated V_{DRM'}, Exponential Waveform, Gate Open, T_J = 125°C)$	dv/dt	10	_	_	V/µs
Critical Rate of Rise of On–State Current $I_{\rm G} = 150~{\rm mA}$, $T_{\rm J} = 125^{\circ}{\rm C}$	di/dt	-	-	100	A/µs

^{4.} Pulse duration $\leq 300~\mu s$, duty cycle $\leq 2\%$.

Ratings apply for tw = 1 ms. See Figure 1 for I_{TM} capability for various durations of an exponentially decaying current waveform.
 tw is defined as 5 time constants of an exponentially decaying current pulse.

^{6.} The gate controlled turn-on time in a crowbar circuit will be influenced by the circuit inductance.



Voltage Current Characteristic of SCR

Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current

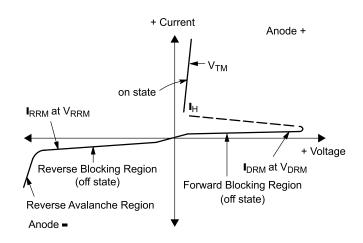


Figure 1. Typical RMS Current Derating

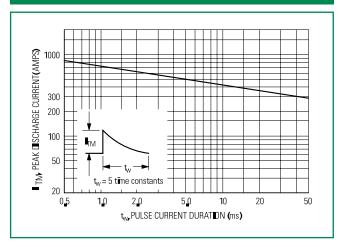


Figure 2. Peak Capacitor Discharge Current Derating

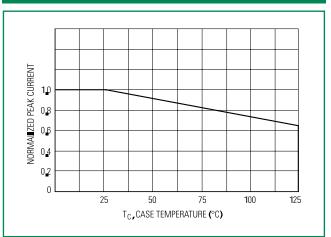


Figure 3. Current Derating

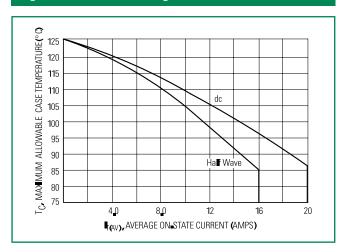
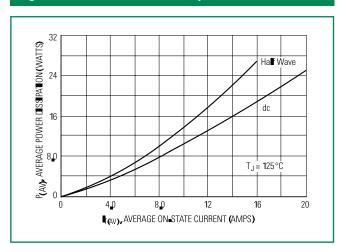


Figure 4. Maximum Power Dissipation







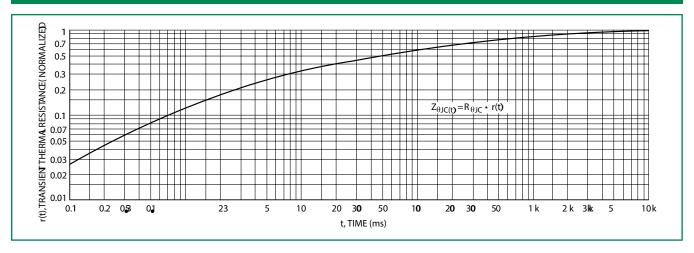


Figure 6.Gate Trigger Current

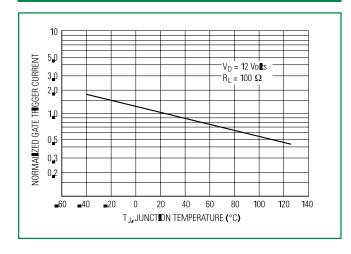


Figure 7. Gate Trigger Voltage

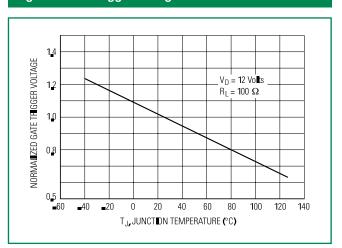
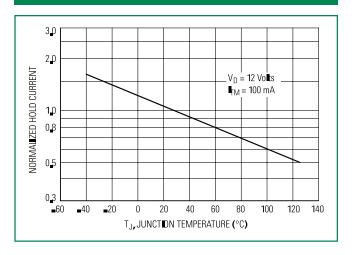
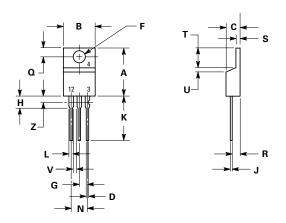


Figure 8. Holding Current

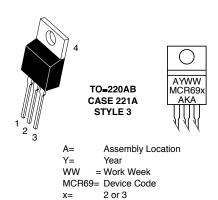




Dimensions



Part Marking System



Location Code

AKA=

6.	Inches		Millimeters		
Dim	Min	Max	Min	Max	
А	0.590	0.620	14.99	15.75	
В	0.380	0.420	9.65	10.67	
С	0.178	0.188	4.52	4.78	
D	0.025	0.035	0.64	0.89	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.41	2.67	
Н	0.110	0.130	2.79	3.30	
J	0.018	0.024	0.46	0.61	
K	0.540	0.575	13.72	14.61	
L	0.060	0.075	1.52	1.91	
N	0.195	0.205	4.95	5.21	
Q	0.105	0.115	2.67	2.92	
R	0.085	0.095	2.16	2.41	
S	0.045	0.060	1.14	1.52	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

Ordering Information

Device	Package	Shipping
MCR69-2	TO-220AB	
MCR69-2G	TO-220AB (Lead-Free)	500 / B
MCR69-3	TO-220AB	500 / Box
MCR69-3G	TO-220AB (Lead-Free)	

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

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